

GF100HF120T2VHE

IGBT Module

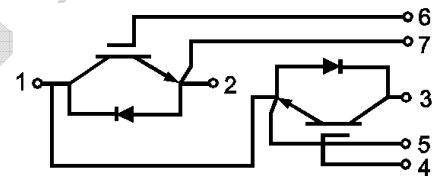
Features:

- Short Circuit Rated >10 μ s
- Low Saturation Voltage: $V_{CE(sat)} = 3.50V @ I_C = 100A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Welding Machine/ Cutting Machine
- Induction Heating
- Ultrasonic Device



Maximum Rated Values of IGBT ($T_C = 25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C,$	100	A
		$T_C = 25^\circ C$	140	A
I_{CM}	Repetitive Peak Collector Current	$T_J = 150^\circ C$	200	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	$T_C = 25^\circ C$ $T_{Jmax} = 150^\circ C$	976	W

Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1\text{mA}$, $V_{CE} = V_{GE}$	4.4	5.2	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{A}$, $V_{GE} = 15\text{V}$	$T_J = 25^\circ\text{C}$	3.50		V
			$T_J = 125^\circ\text{C}$	4.20		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}$, $V_{CE} = V_{CES}$, $T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0\text{V}$, $T_J = 25^\circ\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		12.0		nF
C_{oes}	Output Capacitance			0.96		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}$, $I_C = 100\text{A}$, $R_g = 5\Omega$, $V_{GE} = \pm 15\text{V}$, Inductive Load	$T_J = 25^\circ\text{C}$	288		ns
			$T_J = 125^\circ\text{C}$	289		
t_r	Rise Time		$T_J = 25^\circ\text{C}$	58		ns
			$T_J = 125^\circ\text{C}$	62		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$	305		ns
			$T_J = 125^\circ\text{C}$	318		
t_f	Fall Time		$T_J = 25^\circ\text{C}$	97		ns
			$T_J = 125^\circ\text{C}$	141		
E_{on}	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$	3.5		mJ
			$T_J = 125^\circ\text{C}$	5.2		
E_{off}	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$	2.2		mJ	
		$T_J = 125^\circ\text{C}$	4.0			
Q_g	Total Gate Charge	$T_J = 25^\circ\text{C}$	1110		nC	
		$T_J = 125^\circ\text{C}$	1118			
RBSOA	Reverse Bias Safe Operation Area	$I_C = 200\text{A}$, $V_{CC} = 1050\text{V}$, $V_p = 1200\text{V}$, $R_g = 5\Omega$, $V_{GE} = +15\text{V}$ to 0V , $T_J = 150^\circ\text{C}$	Trapezoid			
SCSOA	Short Circuit Safe Operation Area	$V_{CC} = 600\text{V}$, $V_{GE} = 15\text{V}$, $T_J = 150^\circ\text{C}$	10			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.128		$^\circ\text{C/W}$

Maximum Rated Values of Diode ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current	200	A

Electrical Characteristics of Diode ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F = 100\text{A}$, $V_{GE} = 0\text{V}$	$T_J = 25^\circ\text{C}$	2.35		V
			$T_J = 125^\circ\text{C}$	2.40		
trr	Reverse Recovery Time		$T_J = 25^\circ\text{C}$	137		ns
			$T_J = 125^\circ\text{C}$	272		
I_{rr}	Peak Reverse Recovery Current	$I_F = 100\text{A}$, $di/dt = 1989\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^\circ\text{C}$	67.5		A
			$T_J = 125^\circ\text{C}$	87.5		
Q_{rr}	Reverse Recovery Charge		$T_J = 25^\circ\text{C}$	4.72		μC
			$T_J = 125^\circ\text{C}$	10.06		
E_{rec}	Reverse Recovery Energy		$T_J = 25^\circ\text{C}$	1.96		mJ
			$T_J = 125^\circ\text{C}$	4.43		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.335		$^\circ\text{C}/\text{W}$

Module

Symbol	Description	Min	Typ	Max	Unit
V _{iso}	Isolation Voltage(All Terminals Shorted)	f = 50Hz, 1minute	2500		V
T _J	Maximum Junction Temperature			150	°C
T _{JOP}	Maximum Operating Junction Temperature Range	-40		+150	°C
T _{stg}	Storage Temperature	-40		+125	°C
R _{θCS}	Case-To-Sink (Conductive Grease Applied)		0.03		°C/W
T	Power Terminals Screw:M6	3.0		5.0	N·m
T	Mounting Screw:M6	4.0		6.0	N·m
G	Weight		300		g

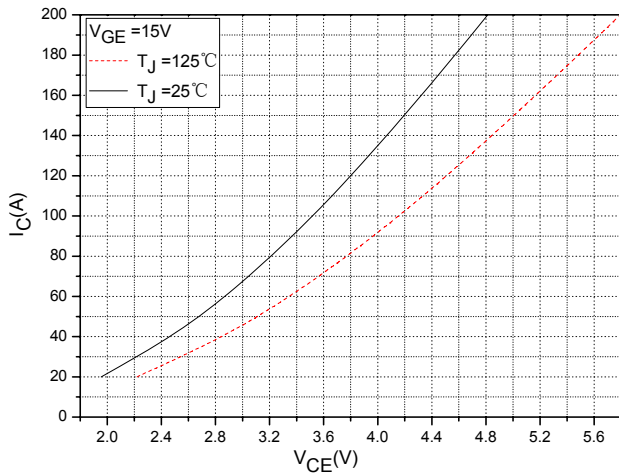


Fig.1 Typical Saturation Voltage Characteristics

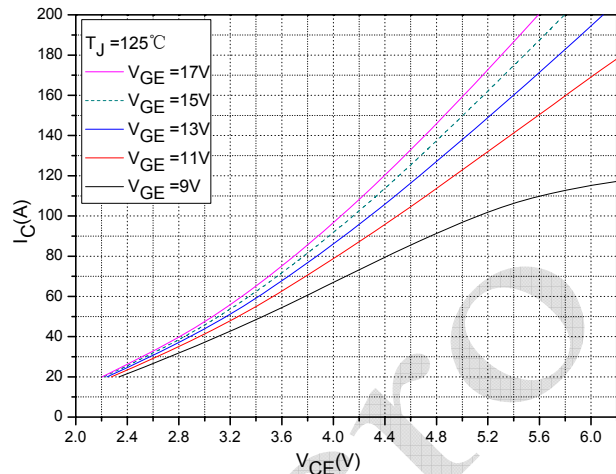


Fig.2 Typical Output Characteristics

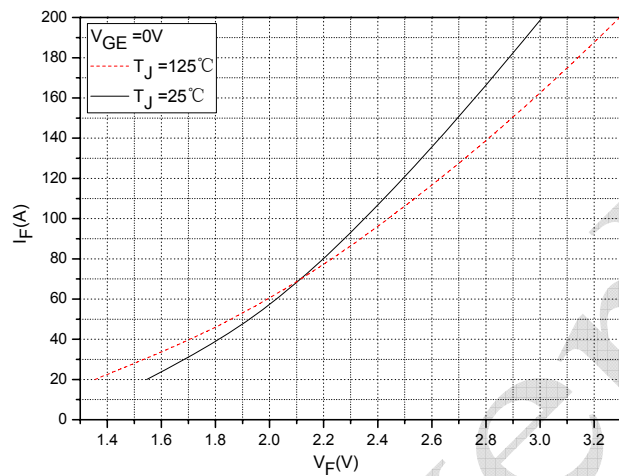


Fig.3 Forward Characteristics of Diode

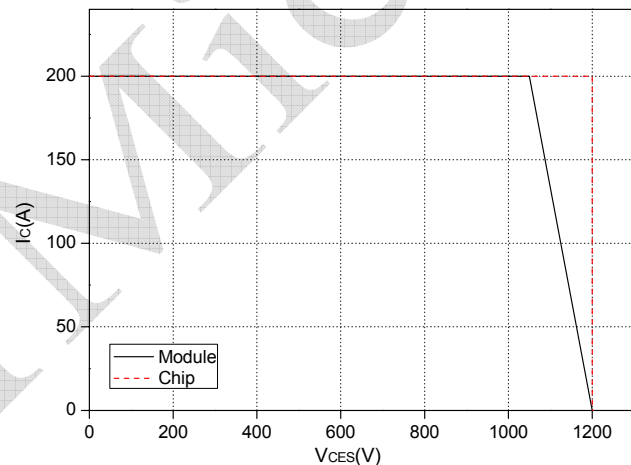


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

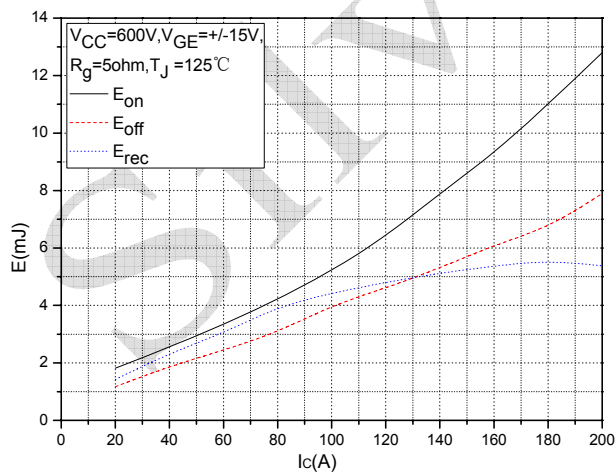


Fig.5 Typical Switching Loss vs. Collector Current

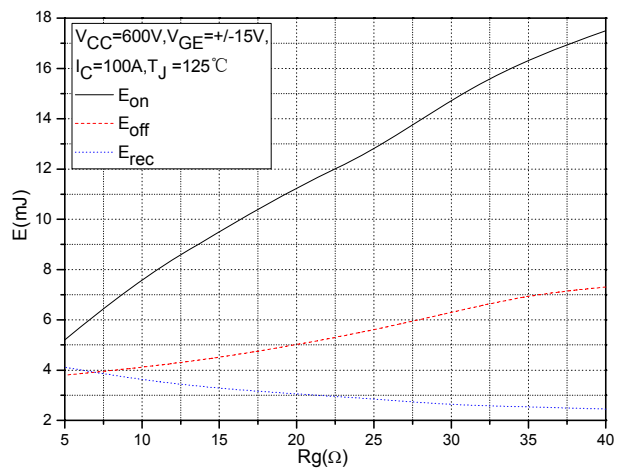


Fig.6 Typical Switching Loss vs. Gate Resistance

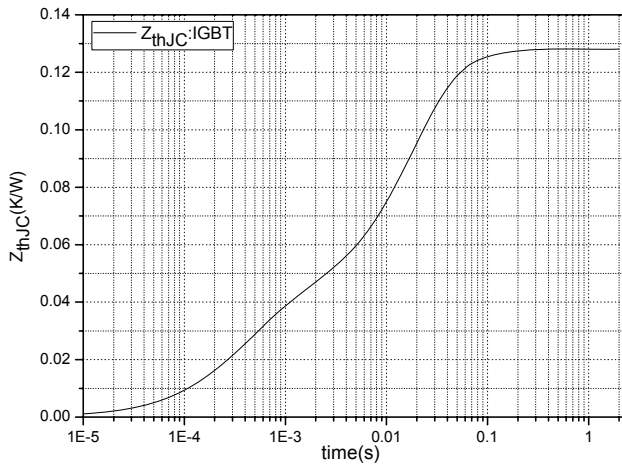


Fig.7 Transient thermal impedance (IGBT)

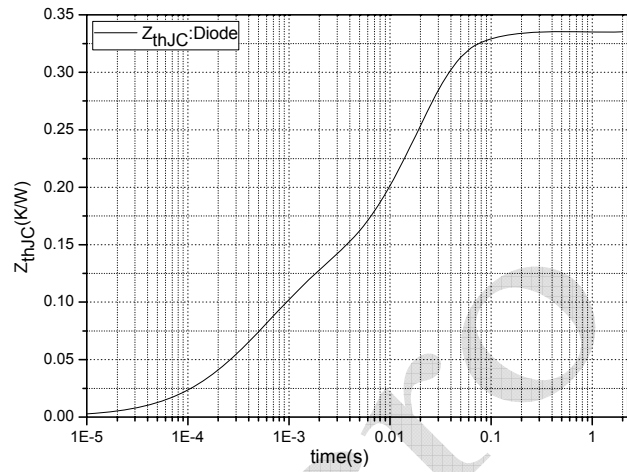


Fig.8 Transient thermal impedance (Diode)

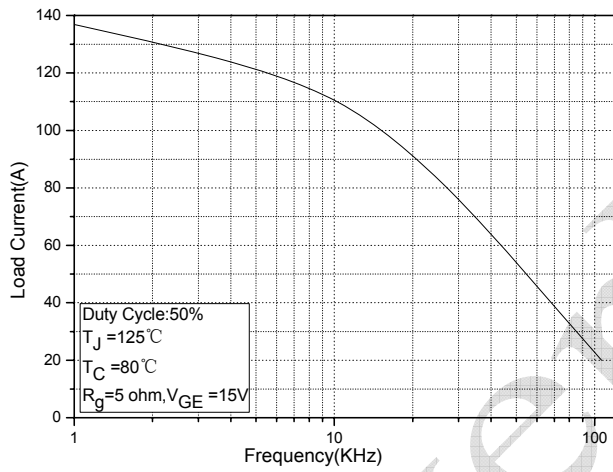
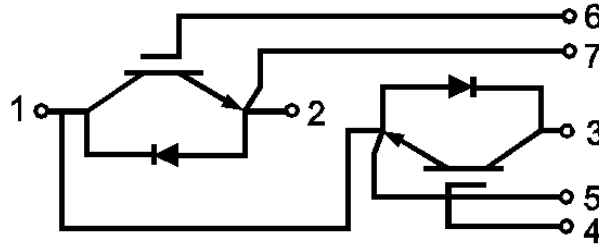
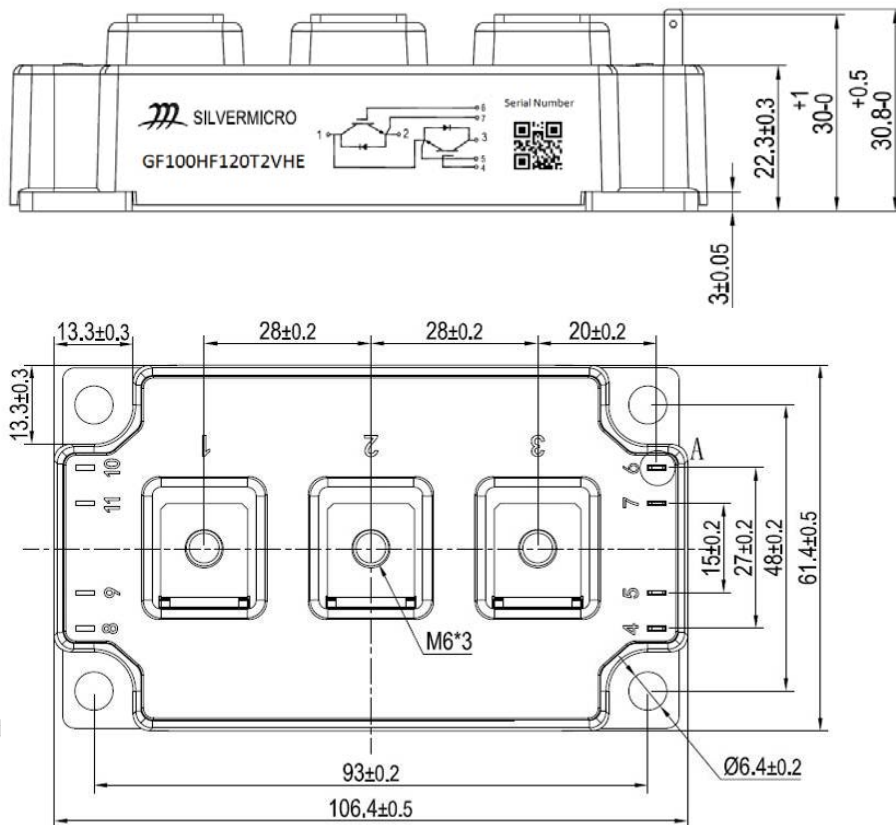


Fig.9 Typical Load Current vs. Frequency

Internal Circuit



Package Outline (Unit: mm):



Announcement

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